MMBT918LT1G

VHF/UHF Transistor

NPN Silicon

Features

 These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V_{CEO}	15	Vdc
Collector - Base Voltage	V_{CBO}	30	Vdc
Emitter - Base Voltage	V_{EBO}	3.0	Vdc
Collector Current - Continuous	Ic	50	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (Note 1) T _A = 25°C Derate above 25°C	P _D	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T _A = 25°C Derate above 25°C	P _D	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

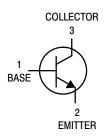
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- 1. $FR-5 = 1.0 \times 0.75 \times 0.062$ in.
- 2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.



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SOT-23 (TO-236) CASE 318 STYLE 6

MARKING DIAGRAM



M3B = Device Code
M = Date Code*
• Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
MMBT918LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MMBT918LT1G

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS			•	
Collector – Emitter Breakdown Voltage $(I_C = 3.0 \text{ mAdc}, I_B = 0)$	V _(BR) CEO	15	_	Vdc
Collector – Base Breakdown Voltage (I _C = 1.0 μAdc, I _E = 0)	V _{(BR)CBO}	30	-	Vdc
Emitter – Base Breakdown Voltage ($I_E = 10 \mu Adc, I_C = 0$)	V _{(BR)EBO}	3.0	_	Vdc
Collector Cutoff Current (V _{CB} = 15 Vdc, I _E = 0)	I _{CBO}	-	50	nAdc
ON CHARACTERISTICS				
DC Current Gain (I _C = 3.0 mAdc, V _{CE} = 1.0 Vdc)	h _{FE}	20	_	_
Collector – Emitter Saturation Voltage (I _C = 10 mAdc, I _B = 1.0 mAdc)	V _{CE(sat)}	-	0.4	Vdc
Base – Emitter Saturation Voltage ($I_C = 10 \text{ mAdc}$, $I_B = 1.0 \text{ mAdc}$)	V _{BE(sat)}	-	1.0	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current – Gain – Bandwidth Product $(I_C = 4.0 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}, f = 100 \text{ MHz})$	f⊤	600	_	MHz
Output Capacitance $(V_{CB} = 0 \text{ Vdc}, I_E = 0, f = 1.0 \text{ MHz})$ $(V_{CB} = 10 \text{ Vdc}, I_E = 0, f = 1.0 \text{ MHz})$	C _{obo}	-	3.0 1.7	pF
Input Capacitance (V _{EB} = 0.5 Vdc, I _C = 0, f = 1.0 MHz)	C _{ibo}	-	2.0	pF
Noise Figure (I _C = 1.0 mAdc, V_{CE} = 6.0 Vdc, R_S = 50 Ω , f = 60 MHz) (Figure 1)	NF	ı	6.0	dB
Power Output (I _C = 8.0 mAdc, V _{CB} = 15 Vdc, f = 500 MHz)	P _{out}	30	-	mW
Common–Emitter Amplifier Power Gain ($I_C = 6.0$ mAdc, $V_{CB} = 12$ Vdc, $f = 200$ MHz)	G _{pe}	11	_	dB

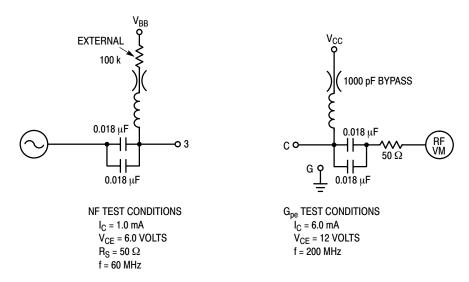
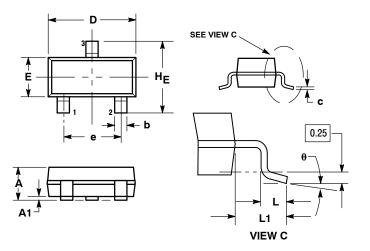


Figure 1. NF, G_{pe} Measurement Circuit 20–200

MMBT918LT1G

PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 **ISSUE AN**



- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH.

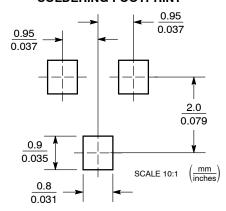
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL. 318-01 THRU -07 AND -09 OBSOLETE, NEW
- STANDARD 318-08.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
С	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.40	2.64	0.083	0.094	0.104

STYLE 6:

- PIN 1. BASE
 - 2. EMITTER
 - COLLECTOR 3.

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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